AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1. (Previously Presented) A process for manufacturing macroelectronics comprising the steps of:

producing thin film active electronics on separate carrier substrates;

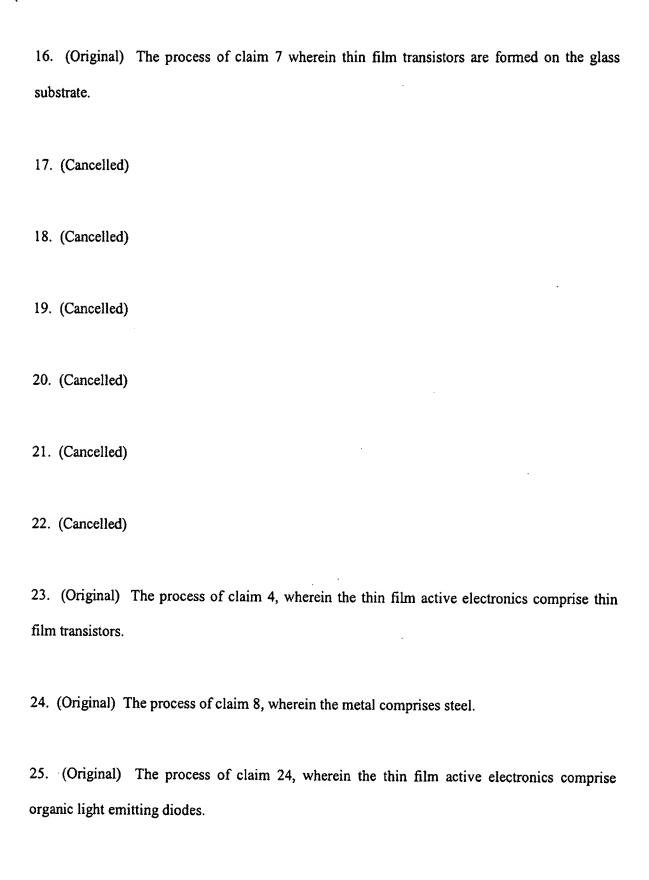
positioning the thin film active electronics in facing relation; and

combining said substrates using anisotropic electrical conductors or light guides so that the thin film active electronics are encapsulated by the anisotropic electrical conductors or the light guides.

- 2. (Original) The process of claim 1 wherein one of said substrates is a flexible foil.
- 3. (Original) The process of claim 1 wherein one of said substrates is a rigid plate.
- 4. (Original) The process of claim 2 wherein the material for one of said substrates is plastic.
- 5. (Original) The process of claim 3 wherein the material for one of said substrates is plastic.
- 6. (Original) The process of claim 2 wherein the material for one of said substrates is glass.

7. (Original) The process of claim 3 wherein the material for one of said substrates is glass. 8. (Original) The process of claim 2 wherein the material for one of said substrates is metal. 9. (Original) The process of claim 3 wherein the material for one of said substrates is metal. 10. (Original) The process of claim 1 wherein the thin film active electronics are produced continuously on separate carrier substrates. 11. (Original) The process of claim 4 wherein organic light emitting diodes are formed on the plastic substrate. 12. (Original) The process of claim 5 wherein organic light emitting diodes are formed on the plastic substrate. 13. (Original) The process of claim 6 wherein organic light emitting diodes are formed on the glass substrate. 14. (Original) The process of claim 7 wherein organic light emitting diodes are formed on the glass substrate. 15. (Original) The process of claim 6 wherein thin film transistors are formed on the glass

substrate.



5

930881.01

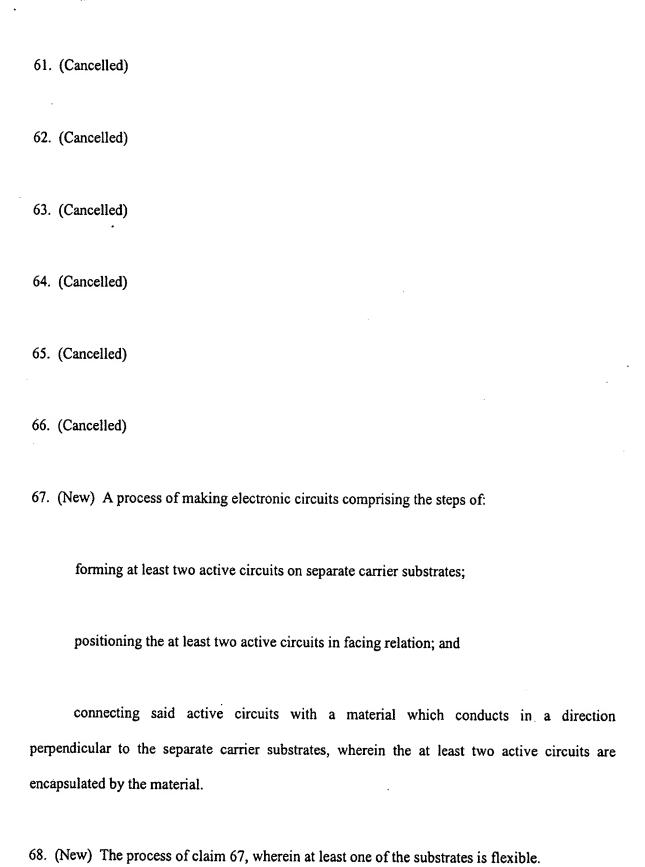
26. (Cancelled) 27. (Cancelled) 28. (Cancelled) 29. (Cancelled) 30. (Cancelled) 31. (Cancelled) 32. (Cancelled) 33. (Cancelled) 34. (Cancelled) 35. (Cancelled) 36. (Cancelled)

37. (Cancelled)

38. (Cancelled)
39. (Cancelled)
40. (Cancelled)
41. (Cancelled)
42. (Previously Presented) The process of claim 1, wherein at least one of the substrates is flexible.
43. (Previously Presented) The process of claim 1, wherein both of the substrates are flexible.
44. (Cancelled)
45. (Cancelled)
46. (Cancelled)
47. (Cancelled)
8. (Cancelled)

49. (Cancelled) 50. (Cancelled) 51. (Cancelled) 52. (Cancelled) 53. (Cancelled) 54. (Cancelled) 55. (Cancelled) 56. (Cancelled) 57. (Cancelled) 58. (Cancelled) 59. (Cancelled)

60. (Cancelled)



- 69. (New) The process of claim 67, wherein both of the substrates are flexible. 70. (New) A method of manufacturing an electronic display comprising the steps of: depositing a transparent conductor on a transparent substrate; forming a thin film organic light emitting diode circuit on said transparent conductor; forming a thin film transistor circuit on a second transparent substrate; positioning the organic light emitting diode and thin film transistor circuits in facing relation; and laminating said circuits to each other. 71. (New) The method of claim 70 wherein said laminating step uses an adhesive anisotropic conductor. 72. (New) The method of claim 71 wherein the conductor is an electrical or optical conductor. 73. (New) The method of claim 71 wherein the bonding layer is the conductor.
- 74. (New) The process of claim 70, wherein at least one of the substrates is flexible.

- 75. (New) The process of claim 70, wherein both of the substrates are flexible.
- 76. (New) A method of manufacturing an electronic circuit comprising the steps of:

forming a first active circuit on a first plane;

forming a second active circuit on a second plane;

positioning the first and second active circuits in facing relation; and

co-laminating said first and second planes with an anisotropic conductor, wherein the anisotropic conductor encapsulates the first and second circuits.

- 77. (New) The process of claim 76, wherein at least one of the planes is flexible.
- 78. (New) The process of claim 76, wherein both of the substrates are flexible.

79. (New) A process for manufacturing macroelectronics comprising the steps of:

producing thin film active electronics on separate carrier substrates;

positioning the active electronics of the carrier substrates in facing relation with respect to each other; and

combining said substrates using anisotropic electrical conductors or light guides, the anisotropic electrical conductors or light guides encapsulating the active electronics.

- 80. (New) The process of claim 79, wherein one of said substrates is a flexible foil.
- 81. (New) The process of claim 79, wherein one of said substrates is a rigid plate.
- 82. (New) The process of claim 80, wherein the material for one of said substrates is plastic.
- 83. (New) The process of claim 81, wherein the material for one of said substrates is plastic.
- 84. (New) The process of claim 80, wherein the material for one of said substrates is glass.
- 85. (New) The process of claim 81, wherein the material for one of said substrates is glass.
- 86. (New) The process of claim 80, wherein the material for one of said substrates is metal.

- 87. (New) The process of claim 81, wherein the material for one of said substrates is metal.
- 88. (New) The process of claim 79, wherein the thin film active electronics are produced continuously on separate carrier substrates.
- 89. (New) The process of claim 82, wherein organic light emitting diodes are formed on the plastic substrate.
- 90. (New) The process of claim 83, wherein organic light emitting diodes are formed on the plastic substrate.
- 91. (New) The process of claim 82, wherein organic light emitting diodes are formed on the glass substrate.
- 92. (New) The process of claim 83, wherein organic light emitting diodes are formed on the glass substrate.
- 93. (New) The process of claim 82, wherein thin film transistors are formed on the glass substrate.
- 94. (New) The process of claim 83, wherein thin film transistors are formed on the glass substrate.

N 11/4 W

- 95. (New) The process of claim 79, wherein at least one of the substrates is flexible.
- 96. (New) The process of claim 79, wherein both of the substrates are flexible.